

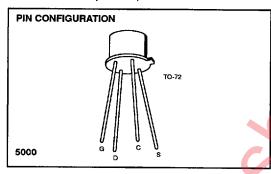
N-Channel JFET High Frequency Amplifier

T.31-25

2N3823

FEATURES

- Low Noise
- Low Capacitance
- Transductance Up to 6500µs



ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted)

Gate-Source or Gate-Drain Voltage
Gate Current 10mA
Storage Temperature Range65°C to +200°C
Operating Temperature Range55°C to +175°C
Lead Temperature (Soldering, 10sec) +300°C
Power Dissipation 300mW
Derate above 25°C2.0mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
2N3823	Hermetic TO-72	-55°C to +175°C
X2N3823	Sorted Chips in Carriers	-55°C to +175°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS	
Igss	Gate Reverse Current		-0.5	nA μA	V	
	Cale / loveled Callella		-0.5		V _{GS} = -20V, V _{DS} = 0	T _A = 150°C
BVGSS	Gate-Source Breakdown Voltage	-30			$I_{G} = -1\mu A$, $V_{DS} = 0$	
VGS(off)	Gate-Source Cutoff Voltage		-8	V	V _{DS} = 15V, I _D = 0.5nA V _{DS} = 15V, I _D = 400μA	
V _{GS}	Gate-Source Voltage	-1.0	-7.5	1		
loss	Saturation Drain Current	4	20	mA	V _{DS} = 15V, V _{GS} = 0	
gfs .	Common-Source Forward Transconductance (Note 1)	3,500	6,500			f = 1kHz
Yfs	Common-Source Forward Transadmittance (Note 2)	3,200				f = 100MHz
gos	Common-Source Output Conductance (Note 1)		35	μs		f = 1kHz
g _{iss}	Common-Source Input Conductance (Note 2)		800		V _{DS} = 15V, V _{GS} = 0	f = 200MHz
goss	Common-Source Output Conductance (Note 2)		200			
Cisa	Common-Source Input Capacitance (Note 2)		6	_	1	f = 1MHz
Cras	Common-Source Reverse Transfer Capacitance (Note 2)		2	pF		
NF 🖣	Noise Figure (Note 2)		2.5	dB	V _{DS} = 15V, V _{GS} = 0 R _G = 1kΩ	f = 100MHz

NOTES: 1. These parameters are measured during a 2ms interval 100ms after DC power is applied.

2. For design reference only, not 100% tested